

Docket No.: 60188-824

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of	:	Customer Number: 20277
	:	
Hisashi NAKAYAMA, et al.	:	Confirmation Number:
	:	
Serial No.:	:	Group Art Unit:
	:	
Filed: March 25, 2004	:	Examiner: Unknown
	:	
For:		SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

**INFORMATION DISCLOSURE STATEMENT**

Mail Stop IDS  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

The relevance of the references listed on attached Form 1449 is discussed in the present specification.

**Serial No.:**

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY



Ramyar M. Farid  
Registration No. 46,692

600 13<sup>th</sup> Street, N.W.  
Washington, DC 20005-3096  
(202) 756-8000 RMF:tlb  
Facsimile: (202) 756-8087  
**Date: March 25, 2004**

INFORMATION DISCLOSURE CITATION IN AN APPLICATION			ATTY. DOCKET NO. <b>60188-824</b>		SERIAL NO.	
			APPLICANT <b>Hisashi NAKAYAMA, et al.</b>			
(PTO-1449)			FILING DATE <b>March 25, 2004</b>		GROUP	
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sub>2</sub> ( <i>if known</i> )	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		US				
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FOREIGN PATENT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number + -Kind Codes ( <i>if known</i> )	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation  Yes      No
		JP P2001-267555A	09/28/2001	MATSUSHITA ELECTRIC IND CO LTD		(Japan w/English Abstract)
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)						
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				
		Ok-Hyun NAM, et al., "Lateral Epitaxy of Low Defect Density GaN Layers Via Organometallic Vapor Phase Epitaxy", American Institute of Physics, Applied Physics Letters 71 (18), pp. 2638-2640, November 3, 1997				
EXAMINER			DATE CONSIDERED			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.